

D-3213

IN THE UNITED STATES PATENT AND TRADEMARK OFFICEPATENT

In re application of:

Calvez et al.

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Group Art Unit: Unknown

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Serial No. 10/550,846

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Examiner: N/A

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Filed: March 24, 2004 (I.A.)

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For: IMPROVEMENTS IN AND
RELATING TO VERTICAL-
CAVITY SEMICONDUCTOR
OPTICAL DEVICES

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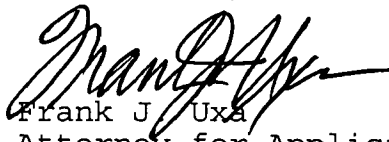
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INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant wishes to call to the attention of the Examiner the documents cited on the accompanying Form PTO-1449. No concession is made that these documents are prior art, and applicant expressly reserves the right to antedate the documents as may be appropriate. Applicant requests that each of these documents be made of record in the above-identified application.

Respectfully submitted,



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U. S. PATENT DOCUMENTS						
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						YES NO
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	AA	W.J. Alford et al., "High Power and good beam quality at 980 nm from a vertical external-cavity surface-emitting laser", <i>Journal of the Optical Society of America B (Optical Physics) Opt. Soc. America USA</i> , Vol. 19, No. 4, pages 663-666 (April 2002).				
	AB	C. Asplund et al, "1260 nm InGaAs vertical-cavity lasers", <i>Electronics Letters</i> , Vol. 38, No. 13, 2002, p.635-636				
	AC	D.I. Babic et al., "Double-fused 1.52- μ m vertical-cavity lasers", <i>Appl. Phys. Lett.</i> (9), 27, 1995, P.1030-1032.				
	AD	W.W. Bewley et al, "Thermal Characterization of Diamond-Pressure-Bond Heat Sinking for Optically Pumped Mid-Infrared Lasers", <i>IEEE Journal of Quantum Electronics</i> , Vol. 35, No. 11, 1999, p. 1597-1601.				
	AE	E. Staffan Björln, "High Gain, High Efficiency Vertical-Cavity Semiconductor Optical Amplifiers", <i>IPRM</i> , 2002, p. 307-310.				
	AF	A. Black, "Wafer Fusion: Materials Issues and Device Results", <i>IEEE Journal Sel. Topics in Quantum Electronics</i> , Vol. 3, No. 3, 1997, p. 943-951.				
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	AH	H. Bourdouce, "Design of Ultra-Fast Dual-Wavelength Resonant-Cavity-Enhanced Schottky Photodetectors", <i>IEEE Journal of Quantum Electronics</i> , Vol. 37, No. 1, 2001, p. 63-68.					
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	AK	R.P. Espindola, "High power, low RIN, spectrally-broadened 14xx DFB pump for application in co-pumped Raman amplification", <i>ECOC</i> , 2001.					
	AL	R.P. Espindola et al., "Penalty-free 10 Gbit/s single-channel co-pumped distributed Raman amplification using low RIN 14xx nm DFB pump", <i>Electron. Letts.</i> , 38, 3, 2002, p. 113.					
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	AN	M.F. Ferreira et al., "Impact of Stimulated Brillouin Scattering on Fibre Raman Amplifiers", <i>Electronics Letters</i> , Vol. 27, No. 17, 1991, p. 1576-1577.					
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	AP	A. Garnache et al., "Sub-500-fs soliton-like pulse in a passively mode-locked broadband surface-emitting laser with 100 mW average power," <i>Applied Physics Letters</i> , Vol. 80, No. 21, 2002, p 3892-3894.			
	AQ	M.D. Gerhold, "Novel Design of a Hybrid-Cavity Surface-Emitting Laser", <i>IEEE Journal of Quantum Electronics</i> , Vol. 34, No. 3, 1998, p. 506-510.			
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	BA	U. Keller, "Semiconductor Saturable Absorber Mirrors (SESAM's) for Femtosecond to Nanosecond Pulse Generation in Solid-State Lasers", <i>IEEE Journal of Sel. Topics in Quant. Electron.</i> , Vol. 2, No. 3, 1996, p. 435-453.			
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	BC	M. Kuznetsov et al, "Design and Characteristics of High-Power (>0.5-W CW) Diode-Pumped Vertical-External-Cavity Surface-Emitting Semiconductor Lasers with Circular TEM ₀₀ Beams", <i>IEEE J of Sel. Topics Quant. Electron</i> , 5, 3, 1999, p. 561.			
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	BF	Z.L. Liao et al., "Nanometer air gaps in semiconductor wafer bonding", <i>Applied Physics Letters</i> , Vol. 78, No. 23, 2001, p. 3726-3728.			
	BG	Z.L. Liao et al., "Semiconductor wafer bonding via liquid capillarity", <i>Applied Physics Letters</i> , Vol. 77, No. 5, 2000, p. 651-653.			
	BH	Y.H. Lo et al., "Semiconductor lasers on Si substrates using the technology of bonding by atomic rearrangement", <i>Appl. Phys. Lett.</i> , Vol. 62(10), 1993, p. 1038-1040.			
	BI	D.J. Lovering et al., "Optimisation of dual-wavelength Bragg mirrors." <i>Electronics Letters</i> , Vol. 32, No. 19, 1996, p. 1782-1784.			
	BJ	M.D. Mermelstein et al., "RIN transfer analysis in pump depletion regime for Raman fibre amplifiers", <i>Electronics Letters</i> , Vol. 38, No. 9, 2002, p. 403-405.			
	BK	P. Michler et al., "Emission Dynamics of In _{0.2} Ga _{0.8} As/GaAs λ and 2 λ Microcavity Lasers", <i>Applied Physics Letters, American Institute of Physics</i> , New York, US, Vol. 68, No. 2, 1996, pages 156-158.			
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	BP	M. Schulze et al, "Efficiency Experts", <i>Photonics Spectra</i> , May 2001.				
	BQ	M. Schulze, "Technologischer Durchbruch mit blauen Festkörperlasern", <i>Photonik</i> 3, 2001.				
	BR	C. Stewen et al., "A 1-k W CW Thin Disc Laser", <i>IEEE J. of Sel. Topics Quant. Electron.</i> , Vol. 6, No. 4, 2000 , p. 650-657.				
	BS	A. Valentini et al., "Organic-inorganic dual-wavelength Bragg reflector", <i>Electronics Letters</i> , Vol. 35, No. 11, 1999 , p. 896-897.				
	BT	E. Yablonovitch et al., "Van der Waals bonding of GaAs epitaxial liftoff films onto arbitrary substrates", <i>Appl. Phys. Lett.</i> , Vol. 56, No. 24, 1990 , p. 2419-2421.				
	BU	F. Yang et al., "Edge-emitting quantum well laser with Bragg reflectors", <i>Appl. Phys. Lett.</i> , Vol. 66, No. 22, 1995 , p. 2949-2951.				
	BV	Coherent Laser Division. Sapphire Optically Pumped Semiconductor Lasers, Copyright 2002, Coherent, Inc.				
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